# Switching (30V, 4.0A) **RTR040N03**

## Features

- 1) Low On-resistance.
- 2) Built-in G-S Protection Diode.
- 3) Small and Surface Mount Package (TSMT3).

#### Application

Power switching, DC / DC converter.

#### Structure

Silicon N-channel MOS FET

### Packaging specifications

	Package	Taping	
Туре	Code	TL	
	Basic ordering unit (pieces)	3000	
RTR040N03	3	0	

## Absolute maximum ratings (Ta=25°C)

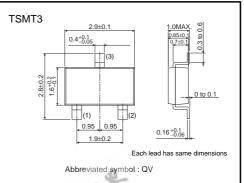
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Parameter		Symbol	Limits	Unit	
Drain-source voltage		VDSS	30	V	
Gate-source voltage		Vgss	12	V	
Droin ourront	Continuous	lo	±4.0	А	
Drain current	Pulsed	I <sub>DP</sub> *1	±16	А	
Source current	Continuous	ls	0.8	А	
(Body diode)	Pulsed	I <sub>SP</sub> *1	16	А	
Total power dissipation		Pd *2	1.0	W	
Channel temperature		Tch	150	°C	
Range of Storage temperature		Tstg	-55 to +150	°C	

\*1 Pw≤10µs, Duty cycle≤1% \*2 Mounted on a ceramic board

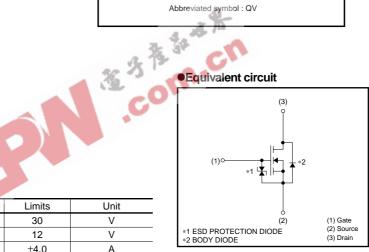
# •Thermal resistance (Ta=25°C)

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth (ch-a)	125	°C / W

# •External dimensions (Unit : mm)



# Equivalent circuit



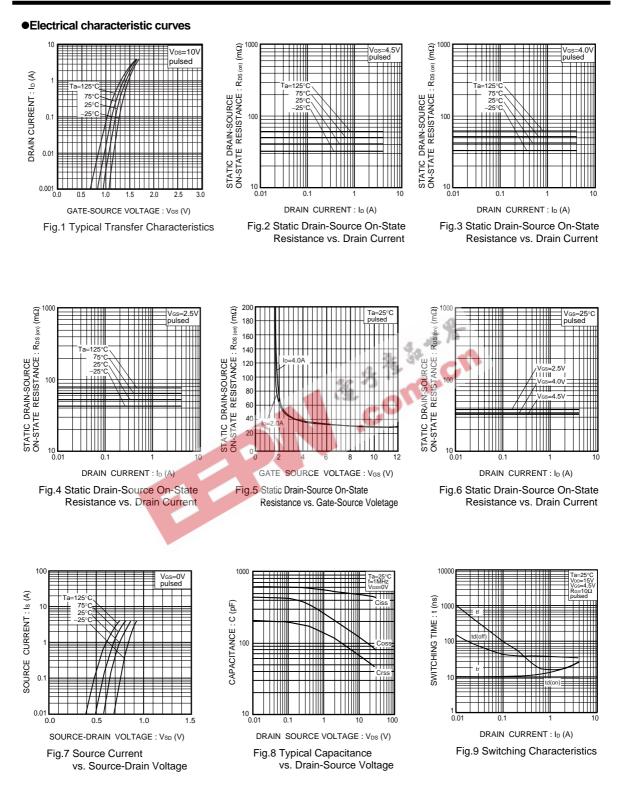
# Transistors

#### •Electrical characteristics (Ta=25°C)

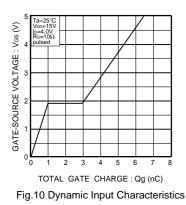
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Gate-source leakage	Igss	-	-	10	μΑ	Vgs=12V, Vds=0V	
Drain-source breakdown voltage	V(BR) DSS	30	-	_	V	I <sub>D</sub> =1mA, V <sub>GS</sub> =0V	
Zero gate voltage drain current	IDSS	-	-	1	μΑ	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V	
Gate threshold voltage	VGS (th)	0.5	-	1.5	V	$V_{DS}=10V$ , $I_{D}=1mA$	
Static drain-source on-state resistance	R <sub>DS</sub> (on)*	-	34	48	mΩ	I <sub>D</sub> =4.0A, V <sub>GS</sub> =4.5V	
		-	36	50	mΩ	I <sub>D</sub> =4.0A, V <sub>GS</sub> =4.0V	
		-	47	66	mΩ	$I_D=4.0A, V_{GS}=2.5V$	
Forward transfer admittance	Y <sub>fs</sub> *	4.0	-	_	S	VDS=10V, ID=4.0A	
Input capacitance	Ciss	-	475	_	pF	VDS=10V	
Output capacitance	Coss	-	120	_	рF	V <sub>GS</sub> =0V	
Reverse transfer capacitance	Crss	-	70	-	рF	f=1MHz	
Turn-on delay time	t <sub>d (on)</sub> *	-	10	-	ns	ID=2.0A	
Rise time	tr *	-	18	-	ns	VDD≒15V	
Turn-off delay time	td (off) *	-	37	-	ns	VGs=4.5V R∟=7.5Ω	
Fall time	tr *	-	19	_	ns	R <sub>G</sub> =10Ω	
Total gate charge	Qg	-	5.9	8.3	nC	V <sub>DD</sub> ≒15V V <sub>GS</sub> =4.5V	
Gate-source charge	Qgs	-	1.0	-	nC	I <sub>D</sub> = 4.0A	
Gate-drain charge	Qgd	-	2.0	-	nC	R∟=3.75Ω R <sub>G</sub> =10Ω	
Pulsed						- 44	
Body diode characteristics (so	urce-drair	n chara	cteristic	·		The ar	
Forward voltage	Vsd	-	-	1.2	V	Is=0.8A, V <sub>GS</sub> =0V	
	3		2			COL	

# RTR040N03

# Transistors



# Transistors



#### Measurement circuits

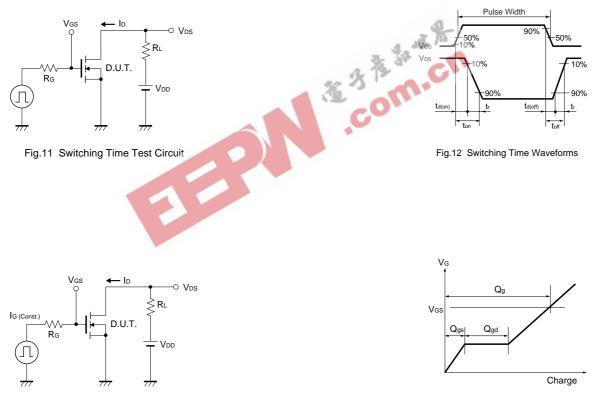


Fig.13 Gate Charge Test Circuit



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